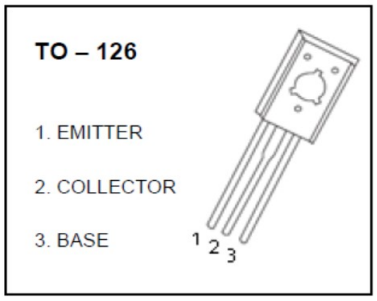
鼎德丰
DING DE FENG

NPN Epitaxial Silicon Transistor

BD435

FEATURES

- Complement to BD436
- Package:TO-126



ABSOLUTE MAXIMUM RATINGS

(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	32	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Collector Peak Current	I_{CM}	7	A
Base Current	I_B	1	A
Collector Dissipation	P_C	1.25	W
Junction Temperature	Tj	150	℃
Storage Temperature	T_{STG}	- 55 ~ 150	℃

ELECTRICAL CHARACTERISTICS

(Ta = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=0.1mA， I_E=0	32		V
Collector-emitter sustaining voltage	$V_{CEO(SUS)}$	I_C=100mA， I_B=0	32		V
Emitter-base breakdown voltage	BV_{EBO}	I_E=0.1mA,I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=32V I_E=0		0.1	mA
Collector cut-off current	I_{CES}	V_{CB}=32V, V_{BE} =0		0.1	mA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0		1	mA
DC current gain	H_{FE1}	V_{CE}=1V ,I_C=500mA	85	140	
	H_{FE2}	V_{CE}=5V ,I_C=10mA	40		
	H_{FE3}	V_{CE}=1V ,I_C=2A	50		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=2A ,I_B=200mA		0.5	V
Base-emitter voltage	V_{BE}	V_{CE}=1V,I_C=2A		1.1	V
Current Gain Bandwidth Product	f_T	V_{CE}=1V,I_C=250mA	3		MHz